

X2G150SD12P3

HIGH POWER SPT+ TYPE
2-PACK IGBT MODULE

XiPosTM
Extra Power Solution

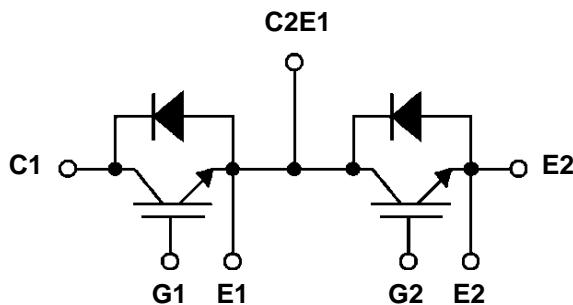


PACKAGE : M3

1200V
150A

PRELIMINARY

CIRCUIT DIAGRAM



FEATURES

- Soft Punch Through (SPT+) Technology
- Fast & soft inverse CAL diodes
- 10us short circuit capability
- Positive $V_{CE(on)}$ temperature coefficient
- Industry standard package

APPLICATIONS

- High power inverter
- Switched mode power supplies (SMPS)
- UPS
- Electrical welding machine

ABSOLUTE MAXIMUM RATINGS

$T_c = 25^\circ\text{C}$, unless otherwise specified

| Symbol | Parameter | Conditions | Ratings | Unit |
|--------------|---------------------------------------|--------------------------|-----------|------------------|
| V_{CES} | Collector-emitter voltage | - | 1200 | V |
| I_C | DC-collector current | $T_c = 25^\circ\text{C}$ | 200 | A |
| | | $T_c = 80^\circ\text{C}$ | 150 | A |
| I_{CRM} | Repetitive peak collector current | 1ms | 300 | A |
| V_{GES} | Gate-emitter peak voltage | - | ± 20 | V |
| I_F | Diode continuous forward current | - | 150 | A |
| I_{FRM} | Diode repetitive peak forward current | - | 200 | A |
| $T_{vj,max}$ | Maximum junction temperature | - | -40 ~ 150 | $^\circ\text{C}$ |
| $T_{vj,op}$ | Operating temperature range | - | -40 ~ 125 | $^\circ\text{C}$ |
| T_{stg} | Storage temperature range | - | -40 ~ 125 | $^\circ\text{C}$ |
| V_{ISOL} | Insulation test voltage | 50Hz, t=1ms | 2.5 | kV |
| M_S | Mounting screw torque | M6 | 3.0 ~ 6.0 | N.m |
| M_t | Mounting terminals screw torque | M6 | 2.5 ~ 5.0 | N.m |

Technical information and specification subject to change without notice.

PRELIMINARY

■ ELECTRICAL CHARACTERISTICS OF IGBT

 $T_j = 25^\circ\text{C}$ unless otherwise specified

| Symbol | Parameter | Min | Typ | Max | Unit | Conditions |
|----------------------|-------------------------------------|------|------|-----|---------------|---|
| $V_{CE(\text{Sat})}$ | C-E saturation voltage | - | 1.8 | - | V | $I_C = 150\text{A}$, $V_{GE} = 15\text{V}$, $T_{vj} = 25^\circ\text{C}$ |
| | | - | 2.0 | - | V | $I_C = 150\text{A}$, $V_{GE} = 15\text{V}$, $T_{vj} = 125^\circ\text{C}$ |
| $V_{GE(\text{th})}$ | G-E threshold voltage | 5.0 | 6.2 | 7.0 | V | $I_C = 4\text{mA}$, $V_{CE} = V_{GE}$ |
| I_{CES} | Zero gate voltage collector current | - | - | 100 | μA | $V_{GE} = 0\text{V}$, $V_{CE} = 1200\text{V}$ |
| I_{GES} | G-E leakage current | -200 | - | 200 | nA | $V_{GE} = \pm 20\text{V}$ |
| R_{Gint} | Internal gate resistance | - | 1.5 | - | Ω | - |
| C_{ies} | Input capacitance | - | 14.0 | - | nF | $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$, $V_{CE} = 25\text{V}$, $T_{vj} = 25^\circ\text{C}$ |
| C_{oes} | Output capacitance | - | 1.22 | - | | |
| C_{res} | Reverse transfer capacitance | - | 1.01 | - | | |
| Q_g | Total gate charge | - | 1560 | - | nC | $V_{GE} = \pm 15\text{V}$ |
| $t_{d(on)}$ | Turn-on delay time | - | 175 | - | ns | $V_{CE} = 600\text{V}$, $I_C = 150\text{A}$, $V_{GE} = \pm 15\text{V}$, $R_G = 6\Omega$, $T_{vj} = 125^\circ\text{C}$ |
| t_r | Turn-on rise time | - | 70 | - | | |
| $t_{d(off)}$ | Turn-off delay time | - | 460 | - | | |
| t_f | Turn-off fall time | - | 70 | - | | |
| E_{ON} | Turn-on Energy loss | - | 10.3 | - | mJ | |
| E_{OFF} | Turn-off Energy loss | - | 7.5 | - | | |

■ ELECTRICAL CHARACTERISTICS OF FRD

 $T_j = 25^\circ\text{C}$ unless otherwise specified

| Symbol | Parameter | Min | Typ | Max | Unit | Conditions |
|----------|-------------------------------|-----|-----|-----|------|--|
| V_F | Diode Forward Voltage Drop | - | 1.6 | - | V | $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 125^\circ\text{C}$ |
| | | - | 1.6 | - | | |
| I_{rr} | Peak Reverse Recovery Current | - | 80 | - | A | $I_F = 150\text{A}$ $V_{CE} = 600\text{V}$ $V_{GE} = 15\text{V}$ |
| Q_{rr} | Diode Recovery Charge | - | 22 | - | | |

■ THERMAL AND MECHANICAL CHARACTERISTICS

 $T_j = 25^\circ\text{C}$ unless otherwise specified

| Symbol | Parameter | Min | Typ | Max | Unit | Condition |
|---------------|--|-----|------|-----|------|-----------|
| $R_{th(j-c)}$ | Junction-to-Case (IGBT Part, Per 1/2 Module) | - | 0.1 | - | °C/W | |
| $R_{th(j-c)}$ | Junction-to-Case (FRD Part, Per 1/2 Module) | - | 0.35 | - | °C/W | |
| $R_{th(c-f)}$ | Case-to-Heat Sink (With Thermal Compound) | - | 0.03 | - | °C/W | |
| Weight | Module | | 320 | | g | |

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PRELIMINARY

■ PERFORMANCE CURVES (I)

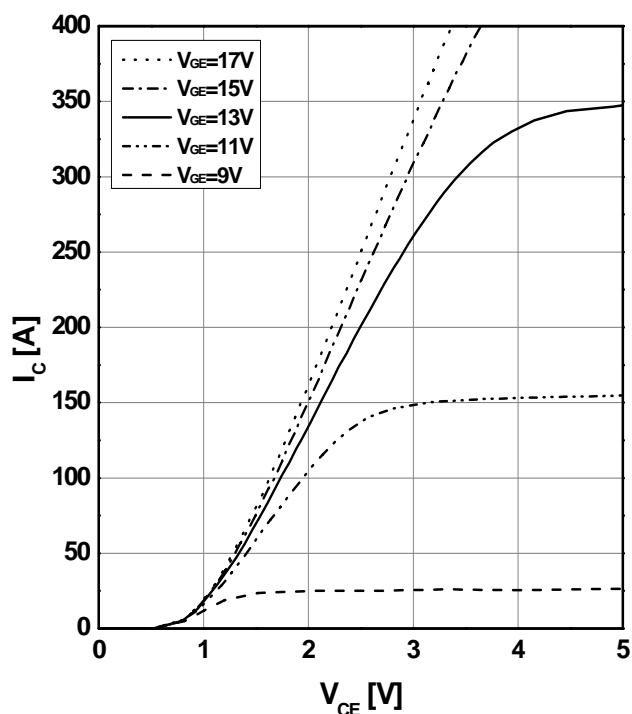


Fig1. Typical Output Characteristics

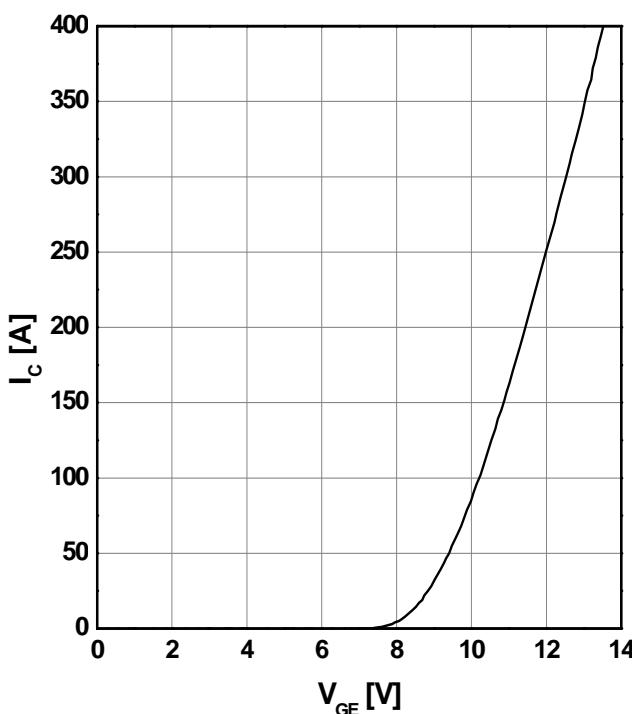


Fig2. Transfer Characteristics

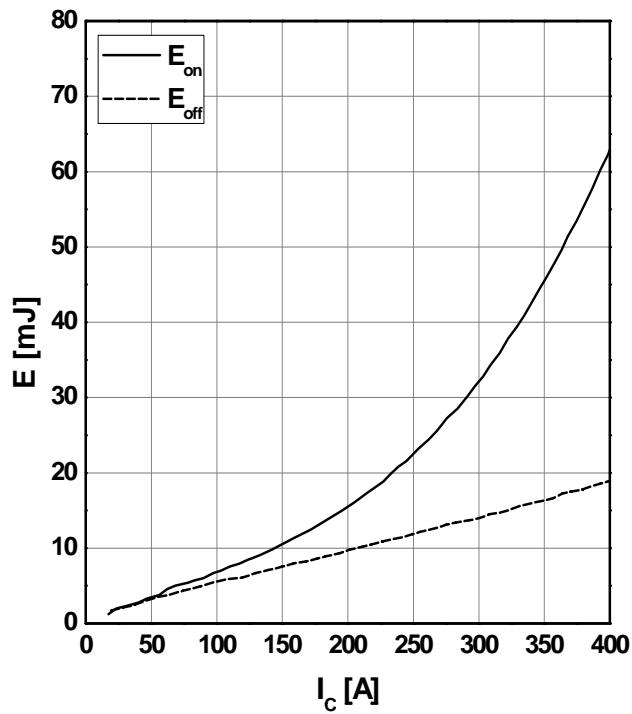


Fig3. Energy Loss vs. I_c

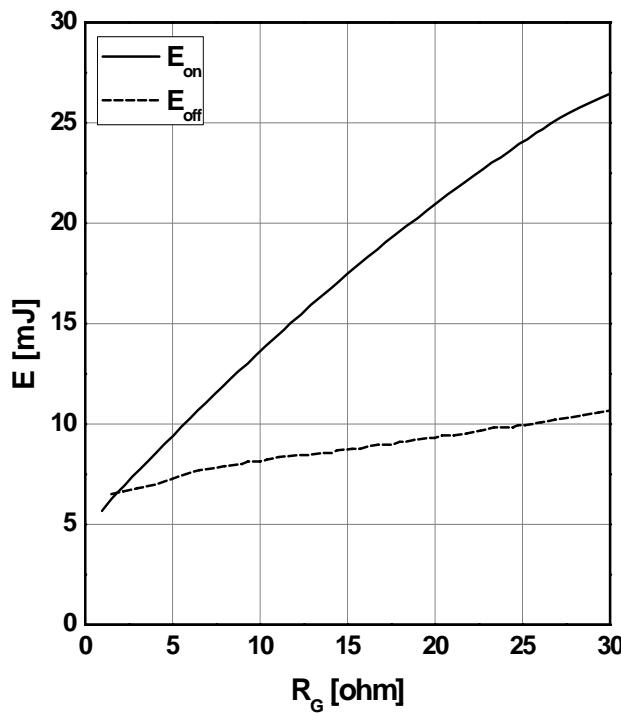


Fig4. Energy Loss vs. R_G

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PRELIMINARY

■ PERFORMANCE CURVES (II)

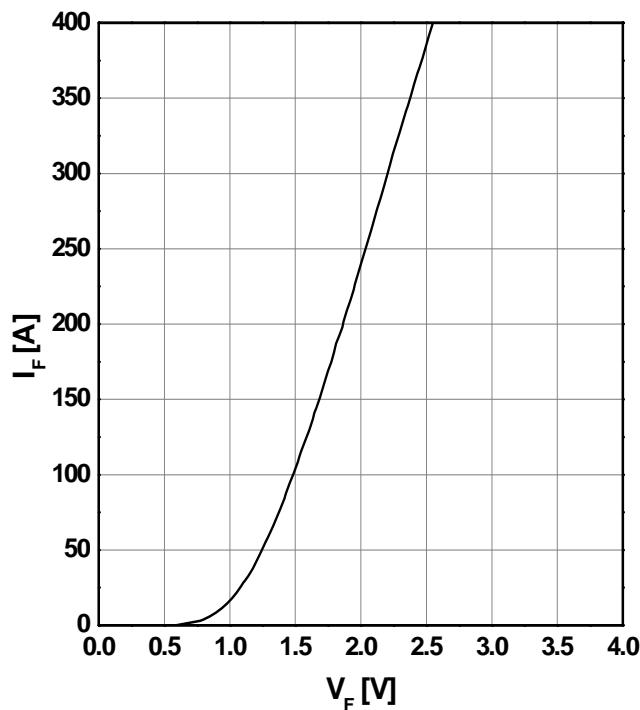


Fig5. DIODE Forward Characteristic

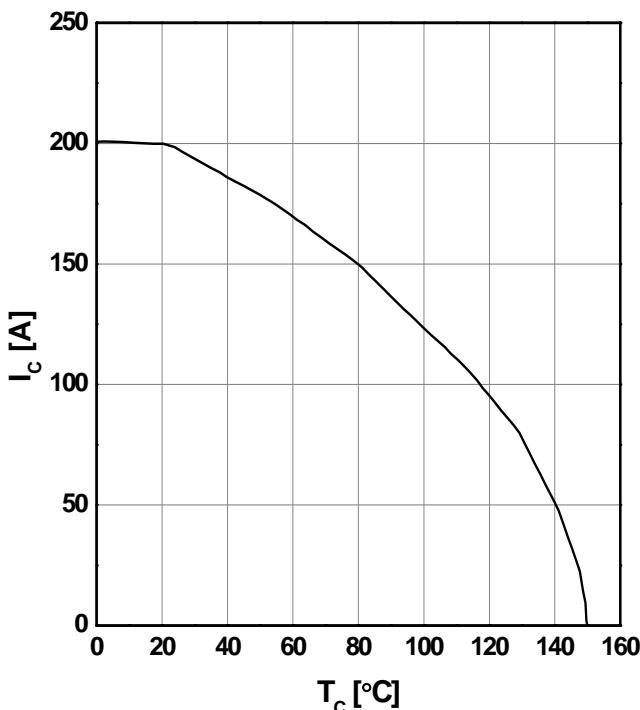


Fig6. Reverse Bios SOA ($T_{vj} = 125^\circ\text{C}$)

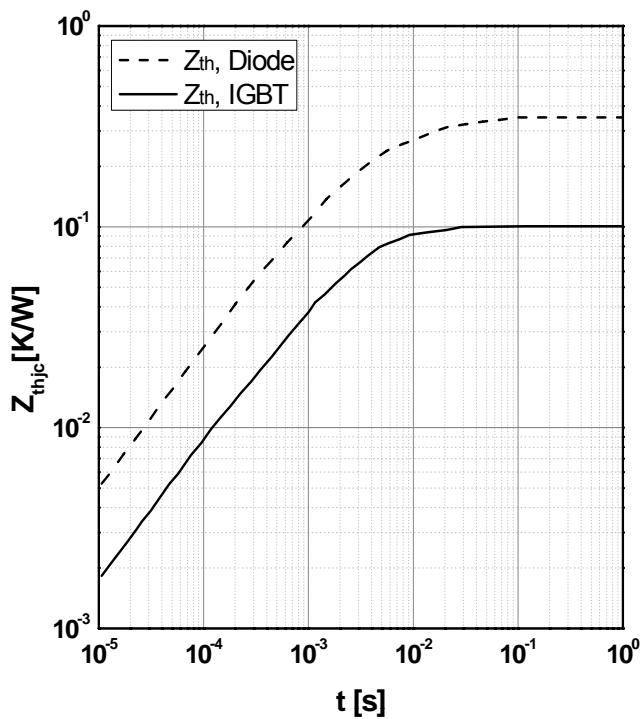


Fig7. Transient Thermal

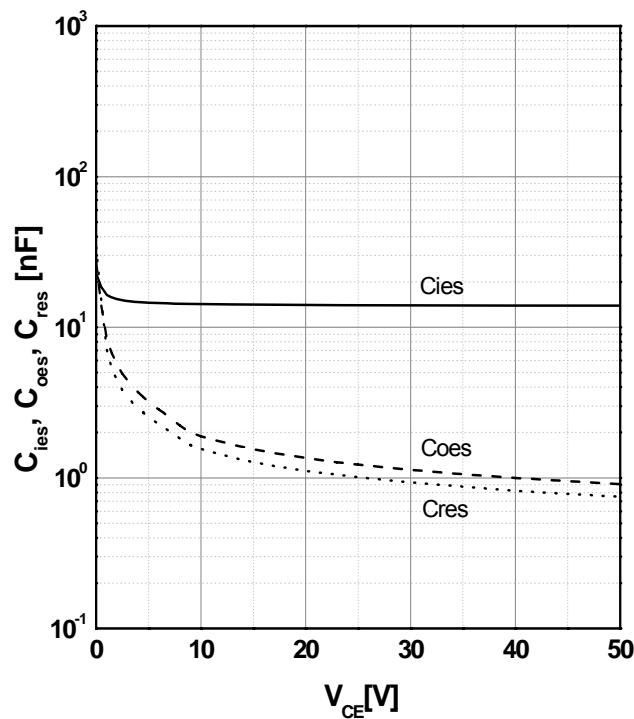
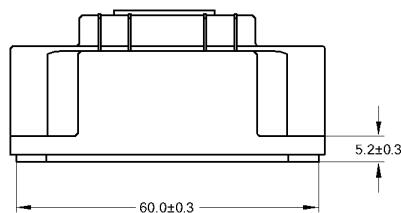
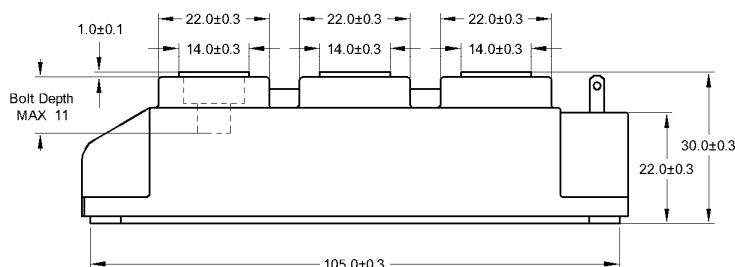
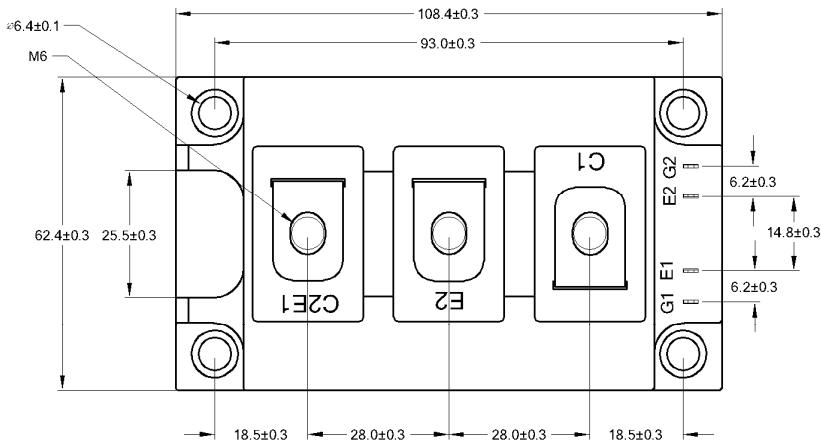


Fig8. Typ. Capacitance

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PRELIMINARY

■ PACKAGE OUTLINES



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